

Silicon NPN Power Transistors

2SC2497 2SC2497A

DESCRIPTION

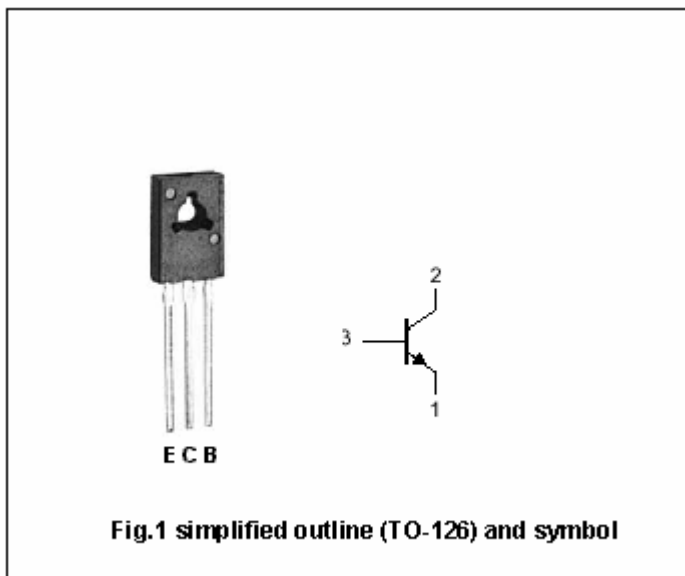
- With TO-126 package
- Complement to type 2SA1096/A
- High collector to emitter voltage V_{CEO}

APPLICATIONS

- For low-frequency power amplification

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	70	V
V_{CEO}	Collector- emitter voltage	2SC2497	50	V
		2SC2497A	60	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
I_{CM}	Collector current-peak		3	A
P_D	Total power dissipation	$T_C=25^\circ C$	1.2^{*1}	W
			5^{*2}	
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		$-55^\circ C+150$	°C

Note) *1: Without heat sink

*2: With a 100 × 100 × 2 mm A1 heat sink

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SC2497	50			V
		2SC2497A	60			
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	70			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A ; I _B =0.15A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1.5A ; I _B =0.15A			1.5	V
I _{CEO}	Collector cut-off current	V _{CE} =10V ; I _B =0			100	μA
I _{CBO}	Collector cut-off current	V _{CB} =20V ; I _E =0			1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			10	μA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	80		220	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =20V, f=1MHz		35		pF
f _T	Transition frequency	I _E =0.5A ; V _{CB} =5V, f=200MHz		150		MHz

◆ h_{FE} Classifications

R	S
80-160	120-220

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PACKAGE OUTLINE

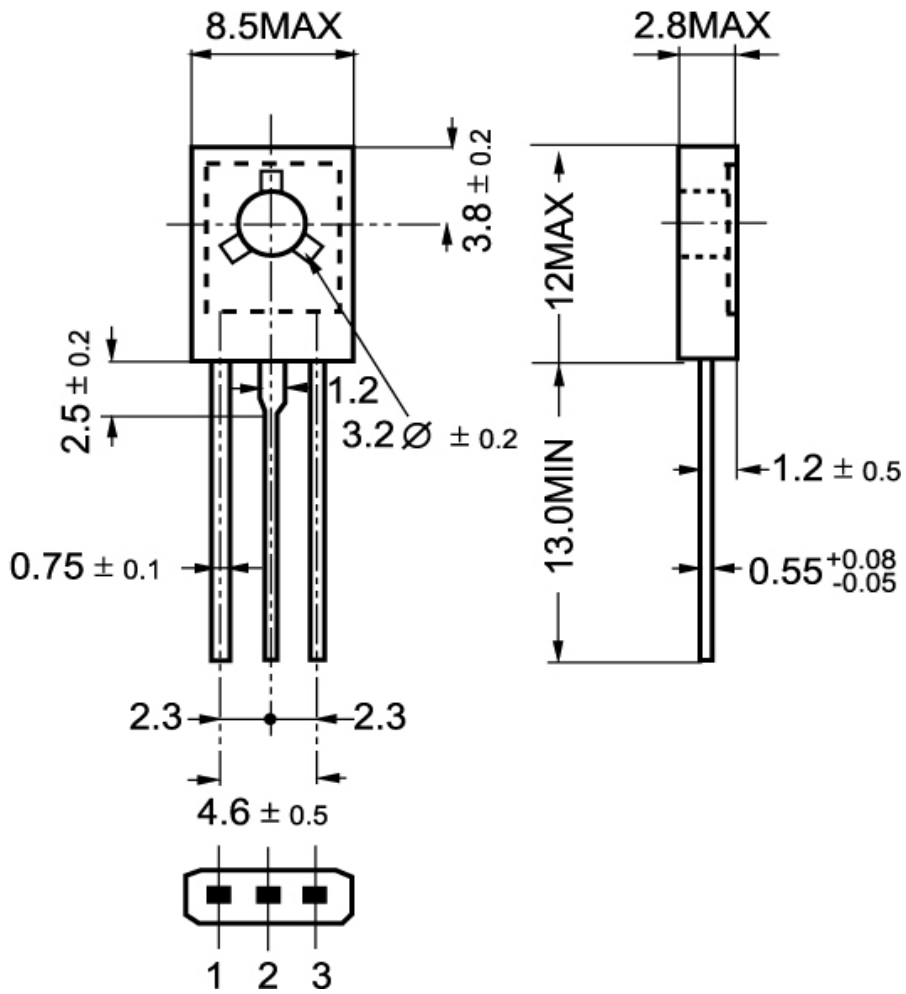


Fig.2 Outline dimensions